Anion-exchange Synthesis of Thermoelectric Layered $SnS_{0.1}Se_{0.9-x}Te_x$ Nano/microstructures in Aqueous Solution; Complexity and Carrier Concentration.[†]; Supporting Information.

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Figure S1. SEM images of $SnS_{0.1}Se_{0.9-x}Te_x$ nano/microstructures revealing the positions where EDS spectra in Figure 2g-i were collected: (a) x = 0.02, (b) x = 0.05, and (c) c = 0.08.



Figure S2. Characterization of $SnS_{0.1}Se_{0.82}Te_{0.08}$ nano/microstructures: (a) HAADF-STEM image and (b-e) its corresponding element maps for Sn, S, Se and Te, respectively.



Figure S3. Characterization of SnS_{0.1}Se_{0.82}Te_{0.08} nano/microstructures: (a) HAADF-STEM image and (b-e) its corresponding element maps for Sn, S, Se and Te, respectively.



Figure S4. (a-c) Rietveld-refined lattice parameters and (d) unit cell volumes as a function of Te concentration (x) for SPS-SnS_{0.1}Se_{0.9-x}Te_x (x = 0.02, 0.05, 0.08). The linear fits to each set of data are indicated by the red dashed/dotted line.



Figure S5. SEM images of $SnS_{0.1}Se_{0.9-x}Te_x$ pellets revealing the positions where EDS spectra in Figure 5g-i were collected: (a) x = 0.02, (b) x = 0.05, and (c) c = 0.08.



Figure S6. Characterization of SPS-SnS $_{0.1}$ Se $_{0.88}$ Te $_{0.02}$: (a) HAADF-STEM image and (b-e) its corresponding element maps for Sn, S, Se and Te, respectively.



Figure S7. Characterization of SPS-SnS_{0.1}Se_{0.82}Te_{0.08} (peeled plate 1): (a) HAADF-STEM image and (b-e) its corresponding element maps for Sn, S, Se and Te, respectively.



Figure S8. Characterization of SPS-SnS_{0.1}Se_{0.82}Te_{0.08} (peeled plate 2): (a) HAADF-STEM image and (b-e) its corresponding element maps for Sn, S, Se and Te, respectively.